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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
09/666,553	09/21/2000	Yasuhiko Nomura	001222	7592	
	7590 07/21/2003		_		
ARMSTRUI	ARMSTRONG,WESTERMAN & HATTORI, LLP 1725 K STREET, NW SUITE 1000			EXAMINER	
SUITE 1000				LEUNG, QUYEN PHAN	
WASHINGTO	ON, DC 20006		ART UNIT	PAPER NUMBER	
			2828		

DATE MAILED: 07/21/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

•	•	Application No.	TAnniinantia
Office Action Summary The MAILING DATE of this communication Period for Reply			Applicant(s)
		09/666,553	NOMURA ET AL.
		Examiner	Art Unit
		Quyen P. Leung	2828
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- External after - If the - If NC - Failur - Any r	ORTENED STATUTORY PERIOD FOR IT MAILING DATE OF THIS COMMUNICAT nsions of time may be available under the provisions of 37 (SIX (6) MONTHS from the mailing date of this communicate period for reply specified above is less than thirty (30) days a period for reply is specified above, the maximum statutory re to reply within the set or extended period for reply will, by eply received by the Office later than three months after the 3d patent term adjustment. See 37 CFR 1.704(b).	ION. CFR 1.136(a). In no event, however, may a reply be timion. s, a reply within the statutory minimum of thirty (30) day, period will apply and will expire SIX (6) MONTHS from	nely filed s will be considered timely. the mailing date of this communication
1)🖂	Responsive to communication(a) filed as	. 20 4 . 4 . 2000	
2a)□	Responsive to communication(s) filed or This action is FINAL .		ل
3)□	/-	This action is non-final.	
	Since this application is in condition for a closed in accordance with the practice upon of Claims	allowance except for formal matters, pronder <i>Ex parte Quayle</i> , 1935 C.D. 11, 45	osecution as to the merits is 53 O.G. 213.
4)⊠	Claim(s) <u>1-20</u> is/are pending in the applic	cation.	
4	a) Of the above claim(s) is/are with	hdrawn from consideration	
5)🛛	Claim(s) <u>8-13, 17-20</u> is/are allowed.	Services Consideration.	
	Claim(s) <u>1,2 and 5</u> is/are rejected.		
	Claim(s) <u>3,4,6,7 and 14-16</u> is/are objected	Lto	
8) 🗌 (Claim(s) are subject to restriction a	nd/or election requirement	
Application	n Papers	ve or olocion requirement.	
9)□ ⊤	he specification is objected to by the Exar	miner.	
10)□ TI	ne drawing(s) filed on is/are: a) a	accepted or b) objected to by the Fyam	iner
	Applicant may not request that any objection to	to the drawing(s) be held in abeyance Sec	37 CFR 1 85/a)
11)[] Th	ie proposed drawing correction filed on _	is: a)□ approved b)□ disapprove	ed by the Examiner
	If approved, corrected drawings are required i	n reply to this Office action	ou by the Examiner.
12)[] }	ne oath or declaration is objected to by the	e Examiner.	
	der 35 U.S.C. §§ 119 and 120		
13) <u> </u>	cknowledgment is made of a claim for for	eign priority under 35 U.S.C. & 119(a)-((d) or (f)
a) <u></u>	All b)☐ Some * c)☐ None of:	3 1 1 2 (2)	, G / G / (1).
1.	Certified copies of the priority docum	ents have been received.	
2.	☐ Certified copies of the priority docume	ents have been received in Application	No
	Copies of the certified copies of the p application from the International the attached detailed Office action for a l	riority documents have been received i	in this National Stage
14) 🗌 Ack	nowledgment is made of a claim for dome	ostic priority and a 25 th 2.2	
۳/ ۱	nowledgment is made of a claim for dome $ bracket{}{ m The translation of the foreign language}{ home}{ m nowledgment is made of a claim for dome}{ home}{ m towledgment}{ m The constant is made of a claim for dome}{ home}{ m towledgment}{ m towledgment}$	Drovisional application has been	The second secon
Notice of	References Cited (PTO-892) Draftsperson's Patent Drawing Review (PTO-948) on Disclosure Statement(s) (PTO-1449) Paper No(s)	4) Interview Summary (P7 5) Notice of Informal Pater 1) Other:	FO-413) Paper No(s) nt Application (PTO-152)
D-326 (Rev. 04	1_O1\	Action Summan	

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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

1. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 4/30/03 has been entered.

Response to Amendment

2. In response to applicant's amendment filed 4/7/03, claims 1, 8, 11 and 17 have been amended. Claims 1-20 are pending.

Response to Arguments

3. Applicant's arguments with respect to claims 1-2, 5 have been considered but are most in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 102

4. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

⁽b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

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5. Claims 1-2, 5 are rejected under 35 U.S.C. 102(b) as being anticipated by Yang et al (5,805,624). Yang et al discloses the claimed invention. Yang et al teaches a nitride-based semiconductor layer (125, see col. 4 lines 18-27 for the nitride-based materials) including an emission layer (109); and a dielectric film (111, see col. 6 lines 23-27 for the dielectric materials of silicon nitride as the nitride and titanium oxide as the oxide) formed on the surface of the nitride-based semiconductor layer (125), wherein the dielectric film (111) contains a nitride (silicon nitride) formed directly on the surface of the nitride-based semiconductor layer (125) while containing an oxide (titanium oxide) formed on the nitride (silicon nitride).

Allowable Subject Matter

- 6. Claims 3-4, 6-7, 14-16 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 7. Claims 8-13, 17-20 are allowed.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Quyen P. Leung whose telephone number is (703) 308-0545. The examiner can normally be reached on 8:30-5:00, M-F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Paul Ip can be reached on (703) 308-3098. The fax phone numbers for the

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organization where this application or proceeding is assigned are (703) 308-7724 for regular communications and (703) 308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Quyen P. Leung Primary Examiner Art Unit 2828

QPL July 14, 2003